

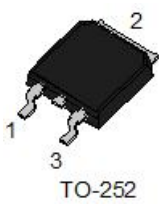

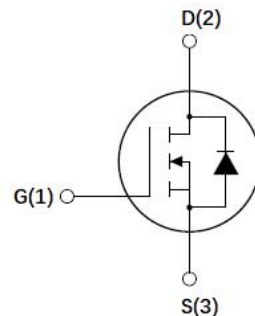


4N65

N-Channel Mode Power MOSFET

<p>Features</p> <ul style="list-style-type: none"> • High Current Rating • Lower R_{DS(ON)} • Fast Switching Capability 	<p>Application</p> <ul style="list-style-type: none"> • Power switching application
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Package

Package Marking and Ordering Information

Product ID	PACK	Qty (pcs)
4N65	TO-252	2500

MAXIMUM RATINGS(Ta=25°C unless otherwise noted)

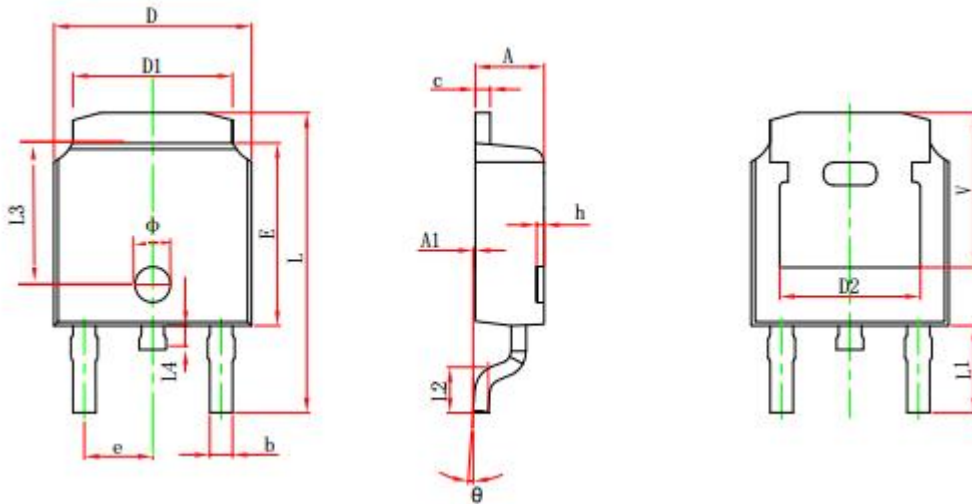
Symbol	Parameter	Value	Unit
V _{DS}	Drain-Source Voltage	650	V
V _{GS}	Gate-Source Voltage	±30	V
I _D	Continuous Drain Current	4.0	A
I _{DM}	Pulsed Drain Current	16	A
E _{AS}	Single Pulsed Avalanche Energy	280	mJ
P _D	Power Dissipation	48	W
T _j	Junction Temperature	-45 to 125	°C
T _{stg}	Storage Temperature		
R _{θJA}	Thermal Resistance From Junction To Ambient	100	°C/W
R _{θJC}	Thermal Resistance From Junction To Case	2.6	°C/W

**4N65*****N-Channel Mode Power MOSFET*****MOSFET ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)**

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Off characteristics						
Drain-Source breakdown Voltage	V(BR)DSS	VGS=0V, ID=250μA	650			V
Drain-Source diode forward Voltage	VSD	VGS=0V, IS=4.0A			1.5	V
Zero gate voltage drain current	IDSS	VDS=650V, VGS=0V			1	μA
Gate-body leakage current	IGSS	VDS=0V, VGS=±30V			±100	nA
On characteristics						
Gate-threshold voltage	VGS(th)	VDS=VGS, ID=250μA	2.0		4.0	V
Non-triggering gate voltage	RDS(on)	VGS=10V, ID=1.0A		2.3	2.6	Ω

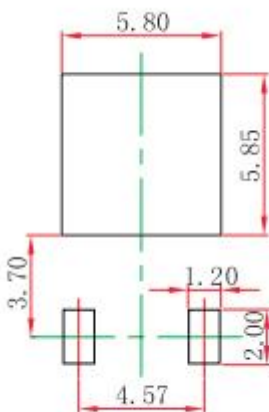


TO-252-2L Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.635	0.770	0.025	0.030
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	4.830 REF.		0.190 REF.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.712	10.312	0.382	0.406
L1	2.900 REF.		0.114 REF.	
L2	1.400	1.700	0.055	0.067
L3	4.460 REF.		0.1756 REF.	
L4	0.600	1.000	0.024	0.039
phi	1.100	1.300	0.043	0.051
theta	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.250 REF.		0.207 REF.	

TO-252-2L Suggested Pad Layout



Note:

1. Controlling dimension: in millimeters.
2. General tolerance: $\pm 0.05\text{mm}$.
3. The pad layout is for reference purposes only.

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